

* **Siddheswar Maikap** 麥凱 教授

所有發表期刊論文

International Journal Papers:

1. S. Chakrabarti, R. Panja, S. Roy, A. Roy, S. Samanta, M. Dutta, S. Ginnaram, **S. Maikap**, H. M. Cheng, L. N. Tsai, Y. L. Chang, R. Mahapatra, D. Jana, J. T. Qiu and J. R. Yang, “Evolution of resistive switching mechanism through H₂O₂ sensing by using TaO_x based material in W/Al₂O₃/TaO_x/TiN structure” *Applied Surface Science*, vol. 433, pp. 51-59, 2018. (Financial supported by **CMRPD2E0091**) (SCI)
2. S. Samanta, **S. Maikap**, A. Roy, S. Jana and J. T. Qiu, “Effect of W/Ir top electrode on resistive switching and dopamine sensing by using optimized TaO_x based memory platform” *Advanced Materials Interfaces*, vol. 4, p. 1700959 (11 pages), 2017. (Financial supported by **MOST-105-2221-E-182-002**) (SCI)
3. S. Samanta, S. Z. Rahaman, A. Roy, S. Jana, S. Chakrabarti, R. Panja, S. Roy, M. Dutta, S. Ginnaram, A. Prakash, **S. Maikap**, H. M. Cheng, L. N. Tsai, J.T. Qiu and S. K. Ray, “Understanding of multi level resistive switching mechanism in GeO_x through redox reaction in H₂O₂/sarcosine prostate cancer biomarker detection” *Scientific. Reports*, vol. 7, p. 11240 (12 pages), 2017. (Financial supported by **MOST-105-2221-E-182-002**) (SCI)
4. S. Chakrabarti, **S. Maikap**, S. Samanta, S. Jana, A. Roy, J. T. Qiu, “Scalable cross point resistive switching memory and mechanism through understanding of H₂O₂/glucose sensing by using IrO_x/Al₂O₃/W structure”, *Phys. Chem. Chem. Phys.*, vol. 19, pp. 25938-25948, 2017. (Financial supported by **CMRPD2E0091**) (SCI)
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7. P. Kumar, **S. Maikap**, S. Ginnaram, J. T. Qiu, D. Jana, S. Chakrabarti, S. Samanta, K. Singh, A. Roy, S. Jana, M. Dutta, Y. L. Chang, H. M. Cheng, R. Mahapatra, H. C. Chiu and J. R. Yang, “Crosspoint resistive switching memory and urea sensing by using annealed GdO_x film in IrO_x/GdO_x/W structure for biomedical applications,” *J. Electrochem. Soc.*, vol. 164, no.4, pp. B127-B135, 2017. (Financial supported by

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